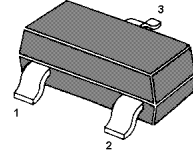


MMBT5400

PNP Silicon Epitaxial Planar Transistor

for high voltage .



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	130	V
Collector Emitter Voltage	$-V_{CEO}$	120	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current Continuous	$-I_C$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	h_{FE}	40	180	-
Collector Base Cutoff Current at $-V_{CB} = 100\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 0.1\text{ mA}$	$-V_{(BR)CBO}$	130	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	120	-	V
Emitter Base Breakdown Voltage at $-I_E = 0.1\text{ mA}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	-	1	V
Current Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$	f_T	100	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF

